RENESAS

NOT RECOMMENDED FOR NEW DESIGNS RECOMMENDED REPLACEMENT PART ISL28233FUZ

DATASHEET

FN6942 Rev 2.00

November 17, 2011

ISL28233I

Dual Micropower, Zero-Drift, RRIO Operational Amplifiers

The ISL28233IUZ is a dual micropower, zero-drift operational amplifier that is optimized for single and dual supply operation from 1.65V to 5.5V and $\pm 0.825V$ to $\pm 2.75V$. The low supply current of 18µA and wide input range enable the ISL28233IUZ to be an excellent general purpose op amp for a range of applications. The ISL28233IUZ is ideal for handheld devices that operate off 2 AA or single Li-ion batteries.

The ISL28233IUZ is available in an industry standard pinout 8 Ld MSOP package. It operates over the temperature range of -40° C to $+85^{\circ}$ C.

Features

- Low Offset Drift 0.06µV/°C, Max
- Quiescent Current (Per Amplifier) 18µA, Typ.
- Single Supply Range +1.65V to +5.5V
- Dual Supply Range ±0.825V to ±2.75V
- Low Noise (0.01Hz to 10Hz) 1.1µV_{P-P}, Typ.
- Rail-to-Rail Inputs and Output
- Operating Temperature Range. . . -40°C to +85°C

Applications

- Bi-Directional Current Sense
- Temperature Measurement
- Medical Equipment
- Electronic Weigh Scales
- Precision/Strain Gauge Sensor
- Precision Regulation
- Low Ohmic Current Sense
- High Gain Analog Front Ends



BI-DIRECTIONAL CURRENT SENSE AMPLIFIER

V_{OS} vs TEMP





Ordering Information

PART NUMBER (Note 3)	PART MARKING	PACKAGE (Pb-Free)	PKG. DWG. #
ISL28233IUZ (Note 2)	8233Z	8 Ld MSOP	M8.118A
ISL28233IUZ-T7 (Notes 1, 2)	8233Z	8 Ld MSOP	M8.118A

NOTES:

1. Please refer to TB347 for details on reel specifications.

2. These Intersil Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

3. For Moisture Sensitivity Level (MSL), please see device information page for <u>ISL282331</u>. For more information on MSL please see techbrief <u>TB363</u>.

Pin Configurations

ISL28233IUZ (8 LD MSOP) TOP VIEW



Pin Descriptions

ISL28233IUZ (8 Ld MSOP)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	IN+_A	Non-inverting input	
5	IN+_B		
	IN+_C		
	IN+_D		
			Circuit 1
4	V-	Negative supply	
2	INA	Inverting input	(See Circuit 1)
6	INB		
	INC		
	IND		
1	OUT_A	Output	V+
7	OUT_B		····-£ī ★
	OUT_C		
	OUT_D		
			Circuit 2
8	V+	Positive supply	

Absolute Maximum Ratings

Max Voltage VIN to GND (V 0.3V) to (V+ + 0.3V)V Max Input Differential Voltage 6.5V Max Input Current .20mA Max Voltage VOUT to GND (10s) .±3.0V ESD Tolerance 4000V Machine Model .400V Charged Device Model .2000V Lateh Lin Desced Part IESD 72P 125°C	Max Supply Voltage V+ to V6.5V
Max Input Current .20mA Max Voltage VOUT to GND (10s) .±3.0V ESD Tolerance	Max Voltage VIN to GND (V 0.3V) to $(V+ + 0.3V)V$
Max Voltage VOUT to GND (10s) ±3.0V ESD Tolerance 400V Human Body Model 400V Machine Model 400V Charged Device Model 2000V	Max Input Differential Voltage 6.5V
ESD Tolerance Human Body Model	Max Input Current
Human Body Model4000VMachine Model400VCharged Device Model2000V	Max Voltage VOUT to GND (10s)±3.0V
Machine Model 400V Charged Device Model 2000V	ESD Tolerance
Charged Device Model	Human Body Model
6	Machine Model 400V
Latch Lip Dassad Dar JESD 79P	Charged Device Model
	Latch-Up Passed Per JESD78B +125°C

Thermal Information

Operating Conditions

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

4. θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

5. For θ_{JC} , the "case temp" location is taken at the package top center.

Electrical Specifications $V_{+} = 5V, V_{-} = 0V, VCM = 2.5V, T_{A} = +25^{\circ}C, R_{L} = 10k\Omega$, unless otherwise specified. Boldface limits apply over the operating temperature range, -40°C to +85°C.

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 6)	түр	MAX (Note 6)	UNIT
DC SPECIFICATI	IONS		1	I	J. J.	
V _{OS}	Input Offset Voltage		-8	±2	8	μV
			-11.9	-	11.9	μV
TCV _{OS}	Input Offset Voltage Temperature Coefficient		-0.06	0.02	0.06	µV/°C
I _{OS}	Input Offset Current		-	1	-	pА
TCI _{OS}	Input Offset Current Temperature Coefficient		-	0.11	-	pA/°C
IB	Input Bias Current		-110	±30	110	pА
			-110	-	110	pА
TCIB	Input Bias Current Temperature Coefficient		-	0.49	-	pA/°C
Common Mode Input Voltage Range		V+ = 5.0V, V- = GND	-0.1	-	5.1	V
CMRR	Common Mode Rejection Ratio	VCM = -0.1V to 5.1V	118	125	-	dB
			115		-	dB
PSRR	Power Supply Rejection Ratio	Vs = 1.65V to 5.5V	110	138	-	dB
			110		-	dB
V _{OH}	Output Voltage Swing, High	$R_L = 10k\Omega$	4.965	4.981	-	V
V _{OL}	Output Voltage Swing, Low			18	35	mV
A _{OL}	Open Loop Gain	$R_L = 1M\Omega$		174	-	dB
V ₊	Supply Voltage	Guaranteed by PSRR	1.65	-	5.5	V
I _S	Supply Current, Per Amplifier	R _L = OPEN	-	18	25	μA
			-	-	35	μA
I _{SC+}	Output Source Short Circuit Current	R_L = Short to ground or V+	13	17	26	mA
I _{SC-}	Output Sink Short Circuit Current		-26	-19	-13	mA



Electrical Specifications

V_+ = 5V, V_- = 0V, VCM = 2.5V, T_A = +25°C, R_L = 10k Ω unless otherwise specified. Boldface limits apply over the operating temperature range, -40°C to +85°C. (Continued)

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 6)	ТҮР	MAX (Note 6)	UNIT
AC SPECIFICATIO	DNS					
GBWP	Gain Bandwidth Product f = 50kHz	$ \begin{array}{l} A_V = 100, \ R_F = 100 k\Omega, \\ R_G = 1 k\Omega, \ R_L = 10 k\Omega \ to \ V_{CM} \end{array} $	-	400	-	kHz
e _N V _{P-P}	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz	-	1.1	-	μV _{P-P}
e _N	Input Noise Voltage Density	f = 1kHz	-	65	-	nV/√(Hz)
i _N	Input Noise Current Density	f = 1kHz	-	72	-	fA/√(Hz)
		f = 10Hz	-	79	-	fA/√(Hz)
C _{in}	Differential Input Capacitance	f = 1MHz	-	1.6	-	pF
Common Mode Input Capacitance		_	-	1.12	-	pF
TRANSIENT RESP	PONSE				1	1
SR	Positive Slew Rate	V_{OUT} = 1V to 4V, R _L = 10kΩ	-	0.2	-	V/µs
	Negative Slew Rate	_	-	0.1	-	V/µs
t _r , t _f , Small Signal	Rise Time, t _r 10% to 90%	$A_V = +1, V_{OUT} = 0.1V_{P-P},$	-	1.1	-	μs
	Fall Time, t _f 10% to 90%	$ \begin{array}{l} R_{F} = 0\Omega, R_{L} = 10 k\Omega, \\ C_{L} = 1.2 pF \end{array} \end{array} $	-	1.1	-	μs
t _r , t _f Large Signal	Rise Time, t _r 10% to 90%	$A_V = +1, V_{OUT} = 2V_{P-P},$	-	8	-	μs
	Fall Time, t _f 10% to 90%	$ \begin{array}{l} R_{F} = 0\Omega, R_{L} = 10 k\Omega, \\ C_{L} = 1.2 pF \end{array} \end{array} $	-	10	-	μs
t _s	Settling Time to 0.1%, 2V _{P-P} Step		-	35	-	μs
t _{recover}	Output Overload Recovery Time, Recovery to 90% of output saturation		-	10.5	-	μs

NOTE:

6. Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.



V+ = 5V, V- = 0V, V_{CM} = 2.5V, RL = Open, T = +25°C, unless otherwise specified.





28

26

24

22

20

18

16

14

12

-40

SUPPLY CURRENT (µA)

N = 30

MAX

MIN

MEDIAN

-20

0

Typical Performance Curves

V+ = 5V, V- = 0V, V_{CM} = 2.5V, R_L = Open, T = +25°C, unless otherwise specified. (Continued)











20

TEMPERATURE (°C)

40

60

 $V_{IN} = 0V$

R_L =OPEN

80









V+ = 5V, V- = 0V, V_{CM} = 2.5V, R_L = Open, T = +25°C, unless otherwise specified. (Continued)

















10

9

8

7

6

5

4

3

2

1

GAIN (dB)







V+ = 5V, V- = 0V, V_{CM} = 2.5V, RL = Open, T = +25°C, unless otherwise specified. (Continued)











FN6942 Rev 2.00 November 17, 2011





V+ = 5V, V- = 0V, V_{CM} = 2.5V, RL = Open, T = +25°C, unless otherwise specified. (Continued)















RENESAS



















FIGURE 35. TCIb HISTOGRAM

V+ = 5V, V- = 0V, V_{CM} = 2.5V, R_L = Open, T = +25°C, unless otherwise specified. **(Continued)**











Applications Information

Functional Description

The ISL28233IUZ uses a proprietary chopper-stabilized technique (see Figure 41) that combines a 400kHz main amplifier with a very high open loop gain (174dB) chopper amplifier to achieve very low offset voltage and drift (2μ V, 0.02μ V/°C typical) while consuming only 18 μ A of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallel-connected, high gain chopper stabilized DC correction amplifier operating at 100kHz. From DC to ~5kHz, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A 5kHz crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the 400kHz gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low 1/f noise. The noise is virtually flat across the frequency range from a few millihertz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

Rail-to-rail Input and Output (RRIO)

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a $10 k \Omega$ load.

IN+ and IN- Protection

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (see Figure 42).



FIGURE 42. INPUT CURRENT LIMITING

Layout Guidelines for High Impedance Inputs

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28233IUZ, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board. The use of guard rings around the amplifier inputs will further reduce leakage currents. Figure 43 shows how the guard ring should be configured. The guard ring does not need to be a specific width, but it should form a continuous loop around both inputs. By setting the guard ring voltage equal to the voltage at the non-inverting input, parasitic capacitance is minimized as well.



FIGURE 43. USE OF GUARD RINGS TO REDUCE

High Gain, Precision DC-Coupled Amplifier

The circuit in Figure 44 implements a single-stage DC-coupled amplifier with an input DC sensitivity of under 100nV that is only possible using a low VOS amplifier with high open loop gain. High gain DC



amplifiers operating from low voltage supplies are not practical using typical low offset precision op amps. For example, the typical $\pm 100\mu V V_{OS}$ and offset drift $0.5\mu V/^{\circ}C$ of a low offset op amp would produce a DC error of >1V with an additional 5mV/°C of temperature dependent error making it difficult to resolve DC input voltage changes in the mV range.

The $\pm 8\mu$ V max V_{OS} and 0.06 μ V/°C of the ISL28233IUZ produces a temperature stable maximum DC output error of only ± 80 mV with a maximum temperature drift of 0.06 μ V/°C. The additional benefit of a very low 1/f noise corner frequency and some feedback filtering enables DC voltages and voltage fluctuations well below 100nV to be easily detected with a simple single stage amplifier.



AMPLIFIER

ISL28233IUZ SPICE Model

Figure 45 shows the SPICE model schematic and Figure 46 shows the net list for the ISL28233IUZ SPICE model. The model is a simplified version of the actual device and simulates important parameters such as noise, Slew Rate, Gain and Phase. The model uses typical parameters from the "Electrical Specifications Table" on page 4. The poles and zeroes in the model were determined from the actual open and closed-loop gain and phase response. This enables the model to present an accurate AC representation of the actual device. The model is configured for ambient temperature of +25°C.

Figures 47 through 54 show the characterization vs simulation results for the Noise Density, Frequency Response vs Close Loop Gain, Gain vs Frequency vs CL and Large Signal Step Response (4V).

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FIGURE 45. SPICE CIRCUIT SCHEMATIC



* Revision I * AC charau *Copyright 2 *Refer to dat *this model ii *terms and p * Connectio * * * * * subckt ISL		9 oltage il Corp ENSE raccep	ooratior STATE otance ense S	n :MENT with th tateme ut	e nt. upply	of upply output 6
D_DN2 R_R21 R_R22 E_EN	102 101 E 104 103 E 0 101 120 0 103 120 8 3 101 10 102 0 0.1V	DN)k)k 3 1 /dc				
R_R1 R_R2 R_R3 R_R4		omosi	sil			
M_M2 + L=50u + W=50u I_I1 4	13 2 11 11 7 DC 92uA 10 DC 100u		sisil			
*Gain stage G_G1 G_G2 R_R5 R_R6 D_D1 D_D2 V_V3	e 4 VV2 13 1 7 VV2 13 1 4 VV2 1.3N VV2 7 1.3N 4 14 DX 15 7 DX VV2 14 0.7 15 VV2 0.7	2 0.00 ∕leg ⁄leg √dc				
G_G4 R_R7 R_R8	st pole 4 VV3 VV2 7 VV3 VV2 4 VV3 1me VV3 7 1me VV3 7 12u	2 16 1 eg				

C_C2 D_D3 D_D4 V_V5 V_V6 *	
*Zero/Po E_E1 G_G5 G_G6 L_L1 R_R12 R_R11 L_L2 R_R9 R_R10 *Pole	le 16 4 7 4 0.5 4 VV4 VV3 16 0.000001 7 VV4 VV3 16 0.000001 20 7 0.3H 20 7 2.5meg VV4 20 1meg 4 19 0.3H 4 19 2.5meg 19 VV4 1meg
G_G7 G_G8 C_C3 C_C4 R_R13 R_R14 *	4 VV5 1meg
*Output S G_G9 G_G10 D_D5 D_D6 D_D7 D_D8 R_R15 R_R16 G_G11 G_G12 *	Stage 21 4 6 VV5 0.0000125 22 4 VV5 6 0.0000125 4 21 DY 4 22 DY 7 21 DX 7 22 DX 4 6 8k 6 7 8k 6 4 VV5 4 -0.000125 7 6 7 VV5 -0.000125

.model pmosisil pmos (kp=16e-3 vto=10m) .model DN D(KF=6.4E-16 AF=1) .MODEL DX D(IS=1E-18 Rs=1) .MODEL DY D(IS=1E-15 BV=50 Rs=1) .ends ISL28233

FIGURE 46. SPICE NET LIST



Characterization vs Simulation Results



FIGURE 47. CHARACTERIZED INPUT NOISE VOLTAGE **DENSITY vs FREQUENCY**



FIGURE 48. SIMULATED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY



FIGURE 49. CHARACTERIZED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

TITIT

 \mathbf{C}_{L}

CL

 $V_{OUT} = 10 \text{mVP-P} \text{ C}_{L} = 3.7 \text{pF}$

 $C_L = 104 pF$

111

10k

C_L = 824pF

= 474pF

= 224pF

11100

100k

C_L = 51pF

FREQUENCY (Hz)

FIGURE 51. CHARACTERIZED GAIN vs FREQUENCY vs

Гþ

1M

10M



FIGURE 50. SIMULATED FREQUENCY RESPONSE vs **CLOSED LOOP GAIN**





FN6942 Rev 2.00 November 17, 2011

CL

8

6

4

2

0

-2

-4

-6

-8

-10

100

V+ = 5V

AV = +1

R_L = 100k

1k

(gp)

GAIN

NORMALIZED

RENESAS

Characterization vs Simulation Results (Continued)





Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
10/8/11	FN6942.2	Removed "UZ" from Device number top of all pages.
8/23/10	FN6942.1	Removed all ISL28433 device information from data sheet. Stamped not recommended for new designs since these parts are going to be obsolete. Recommended replacement part ISL28233FUZ.
3/25/10	FN6942.0	Initial Release.

Products

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*For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: <u>ISL282331</u>

To report errors or suggestions for this datasheet, please go to www.intersil.com/askourstaff

FITs are available from our website at http://rel.intersil.com/reports/search.php

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Package Outline Drawing

M8.118A

8 LEAD MINI SMALL OUTLINE PLASTIC PACKAGE (MSOP) Rev 0, 9/09









SIDE VIEW 1





NOTES:

- 1. Dimensions are in millimeters.
- 2. Dimensioning and tolerancing conform to JEDEC MO-187-AA and AMSE Y14.5m-1994.
- 3. Plastic or metal protrusions of 0.15mm max per side are not included.
- 4. Plastic interlead protrusions of 0.25mm max per side are not included.
- 5. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 6. This replaces existing drawing # MDP0043 MSOP 8L.

